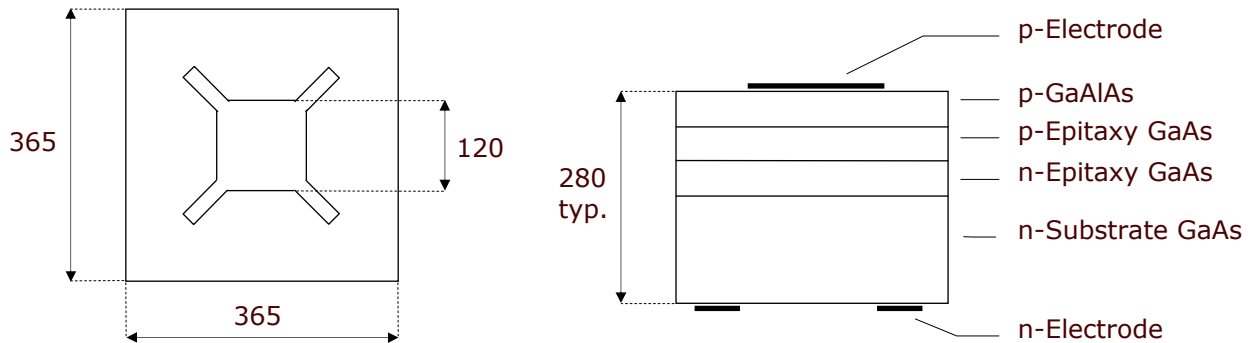


INFRA-RED

Item No.: 131244

1. This specification applies to GaAs / GaAs LED Chips with GaAlAs window - layer
2. Structure
 - 2.1 Mesa structure
 - 2.2 Electrodes

p-side (anode)	Au alloy
n-side (cathode)	Au alloy
3. Outlines (dimensions in microns)



4. Electrical and optical characteristics (T=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage	V_F	$I_F = 20 \text{ mA}$		1,25	1,45	V
Reverse current	I_R	$I_R = 5 \text{ V}$			10	μA
output Power *	Φ_e	$I_F = 20 \text{ mA}$	3,0			mW
		$I_F = 50 \text{ mA}$	7,5			
Switching time	t_r, t_f	$I_F = 20 \text{ mA}$		500		ns
Peak wavelength	λ_p	$I_F = 20 \text{ mA}$		950		nm

Power measurement at OSA on gold plate

5. Packing
 - 1) wire bond side on top
 - 2) back contact on top
6. Labeling

Type	Lot No.	Φ_e typ	Quantity
		min	
		max	